Sheet <u>1</u> of 1

FORM PTO-1449

U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE

LIST OF REFERENCES CITED BY APPLICANT

(Use several sheets if necessary)

ATTY. DOCKET NO. 59553.00019

New Application

APPLICANT

TARRANT et al

FILING DATE

GROUP

December 12, 2005

Not yet assigned

			U.S. PATEN	T DOCUMENTS			
EXAMINER INITIAL		DOCUMENT NO.	DATE	NAME	CLASS	SUB- CLASS	FILING DATE
	AA						
	AB						

FOREIGN PATENT DOCUMENTS

		DOCUMENT NO.	DATE	COUNTRY	CLASS	SUB- CLASS	TRA YES	 ATION PART.
/MK/	AC	0 890 661 A1	01/13/99	European			xx	
	AD							
	A E							

OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc.)

/MK/ 	AF	Weinstein et al, "A class of chemical pinning January 1, 2003, pages 438-444, XP0043992	centers including two elements foreign to HTS" Physica C, Vol. 383, no. 4, 26.		
000000000000000000000000000000000000000	AG	Weinstein et al, "Very High values of Jc obta December 15, 2002, pages 214-222, XP0043	ined in NdBa2Cu30x by use of the U/n process" Physica C., vol. 383, no. 3, 91510.		
000000000000000000000000000000000000000	АН	Babu et al, "Effect of the addition of depleted Physica C., Vol. 372-376, August 2002, page	U02 on the microstructure of melt processed Y-Ba-Cu-O superconductors" s 1183-1186, Xp004375638.		
0,0000	AI		einstein et al, "The role of uranium, with and without irradiation, in the achievement of Jc {300,000 A cm<-2> at 77 K in ge grain melt-textured Y123", Materials Science and Engineering B, ElSevier Sequoia, vol. 53, no. 1-2, May 1, 1998, ges 38-44, XP004139989.		
V	AJ	Sawh R-P et al, "Uranium chemistry and pinning centers in high temperature superconductor", Physica C., vol. 305, no. 3-4, September 1, 1998 pages 159-166, XP004150793.			
/MK/	AK	Weinstein et al, "Properties of HTS for Successful U/n Processing", Physica C, vol. 341-348, November 2000, pages 1415 1418, XP004315950.			
	IER		DATE CONSIDERED		

whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.